

■ PRODUCT CHARACTERISTICS

V_{DSS}	-20V
$R_{DS(on)}$ Typ(@ $V_{GS}=-2.5V$)	16.5mΩ
$R_{DS(on)}$ Typ(@ $V_{GS}=-4.5V$)	13mΩ
I_D	-10A

■ APPLICATIONS

PWM applications

Load switch

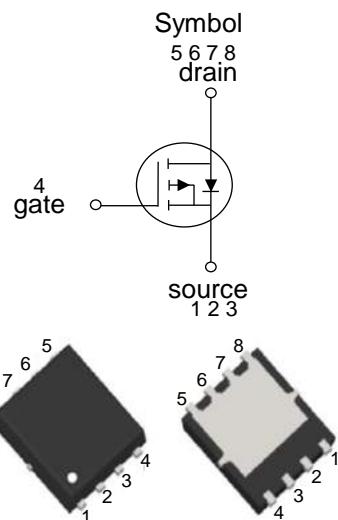
Power management

■ FEATURES

High power and current handing capability

Led free product is acquired

Surface mount package



PDFN3X3-8L

■ ORDER INFORMATION

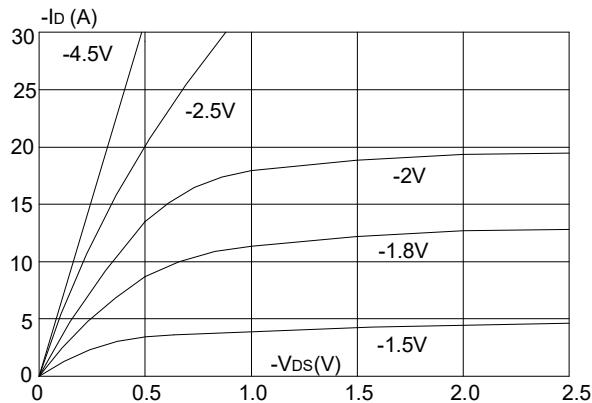
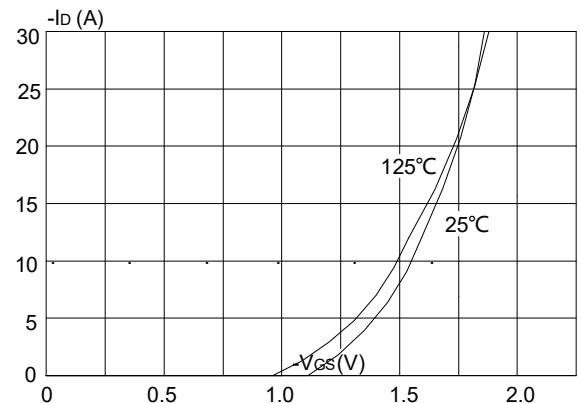
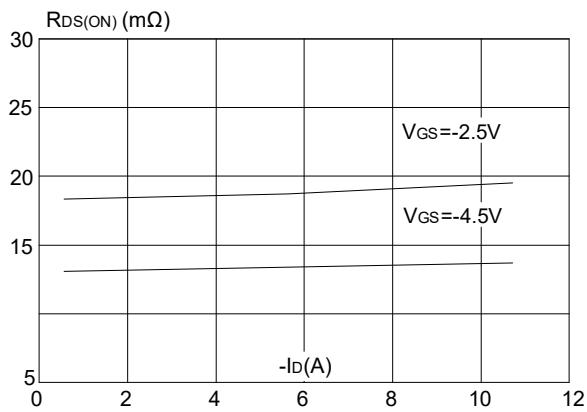
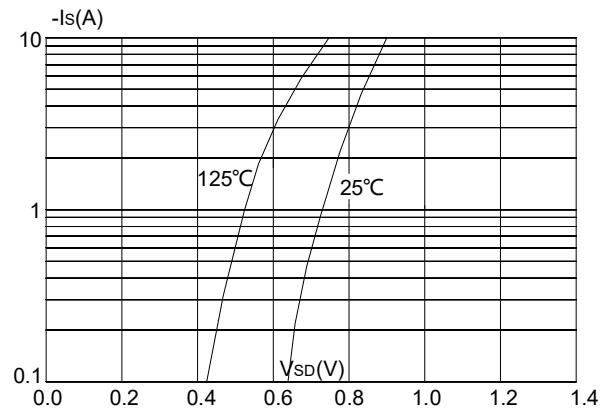
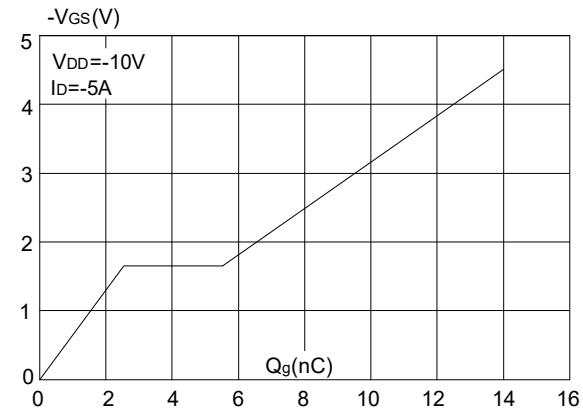
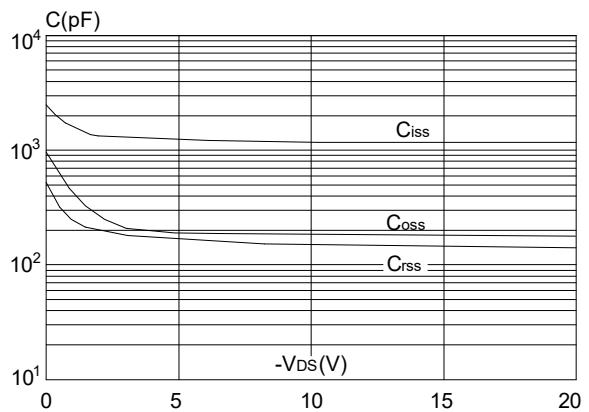
Order codes		Package	Packing
Halogen-free	Halogen		
N/A	MOT2718J	PDFN3X3-8L	5000pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS($T_C=25^\circ C$, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DSS}	-20	V
Gate-source voltage	V_{GSS}	± 12	V
Continuous drain current	I_D	-10	A
Continuous drain current($T_C=100^\circ C$)	I_D	-6.5	A
Pulsed drain current	I_{DM}	-40	A
Single pulsed avalanche energy	E_{AS}	25	mJ
Power dissipation	P_D	13	W
Thermal resistance ,junction to case	$R_{\theta JC}$	9.3	°C/W
Junction temperature	T_J	+150	°C
Storage temperature	T_{STG}	-55~+150	°C

■ ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{DS}}=-250\mu\text{A}$	-20	-	-	V
Drain-source leakage current	I_{DSS}	$\text{V}_{\text{DS}}=-20\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	-1	$\text{n}\Omega$
Gate-source leakage current	I_{GSS}	$\text{V}_{\text{GS}}=\pm 20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-	100	$\text{n}\Omega$
On characteristics						
Gate threshold voltage	$\text{V}_{\text{GS}(\text{th})}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_{\text{DS}}=-250\mu\text{A}$	-0.4	-	-1	V
On-state characteristics	$\text{R}_{\text{DS}(\text{ON})}$	$\text{V}_{\text{GS}}=-2.5\text{V}, \text{I}_{\text{D}}=-4\text{A}$	-	16.5	23	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_{\text{D}}=-7\text{A}$	-	13	18	$\text{m}\Omega$
Forward transconductance	g_{FS}	$\text{V}_{\text{DS}}=-10\text{V}, \text{I}_{\text{D}}=-3\text{A}$	5	-	-	S
Dynamic characteristics						
Input capacitance	C_{iss}	$\text{V}_{\text{GS}}=0\text{V}, \text{V}_{\text{DS}}=-10\text{V}$ $f=1\text{MHz}$	-	1200	-	pF
Out capacitance	C_{oss}		-	191	-	pF
Reverse transfer capacitance	C_{rss}		-	168	-	pF
Switching characteristics						
Total gate charge	Q_g	$\text{V}_{\text{GS}}=-4.5\text{V}, \text{V}_{\text{DS}}=-10\text{V}$ $\text{I}_{\text{D}}=-5\text{A}$	-	14	-	nC
Gate-source charge	Q_{gs}		-	2.5	-	nC
Gate-drain charge	Q_{gd}		-	3	-	nC
Turn-on delay time	$\text{t}_{\text{d}(\text{on})}$	$\text{V}_{\text{DD}}=-10\text{V}, \text{I}_{\text{D}}=-5\text{A}$ $\text{R}_G \leq 10 \Omega \quad \text{V}_{\text{GS}}=-4.5\text{V}$	-	13	-	nS
Turn-on rise time	t_r		-	52	-	nS
Turn-off delay time	$\text{t}_{\text{d}(\text{off})}$		-	103	-	nS
Turn-off fall time	t_f		-	81	-	nS
Source-drain diode ratings and characteristics						
Continuous diode forward current	I_{SD}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{SD}}=-10\text{A}$	-	-	-10	A
Diode forward current	V_{SD}		-	-	-1.2	V

■ TYPICAL CHARACTERISTICS

Figure 1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics

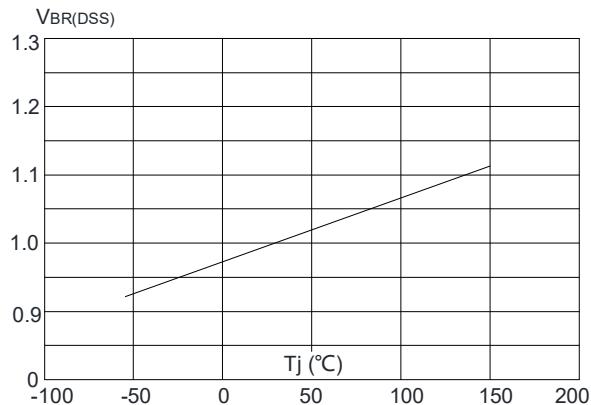
■ TYPICAL CHARACTERISTICS(Cont.)


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

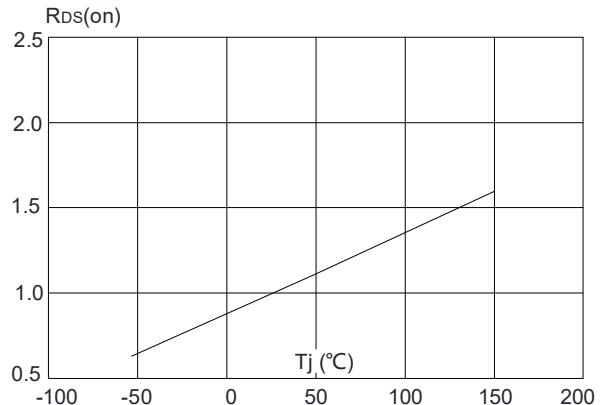


Figure 8: Normalized on Resistance vs. Junction Temperature

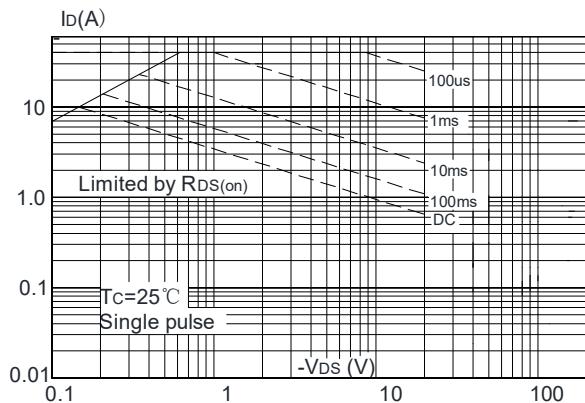


Figure 9: Maximum Safe Operating Area

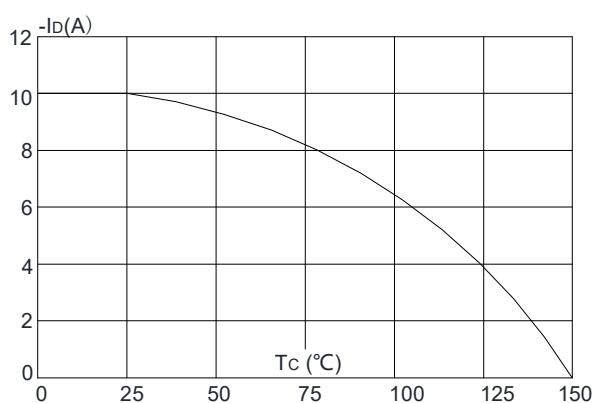


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

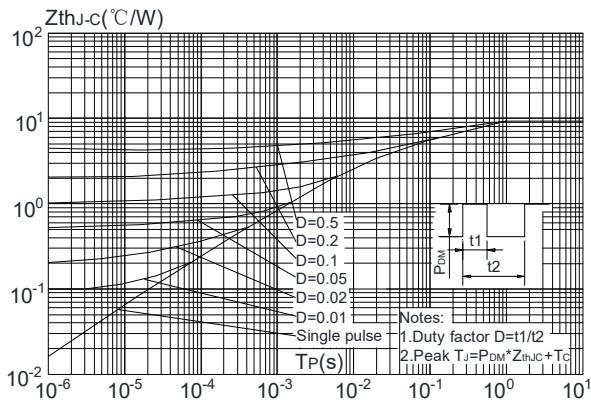


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

■ PDFN3X3-8L PACKAGE MECHANICAL DATA
